

MOS FIELD EFFECT TRANSISTOR **2SJ648**

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The 2SJ648 is a switching device which can be driven directly by a 2.5 V power source.

The 2SJ648 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance

RDS(on)1 = 1.45 Ω MAX. (VGS = -4.5 V, ID = -0.2 A)

 $R_{DS(on)2} = 1.55 \Omega MAX. (V_{GS} = -4.0 V, I_{D} = -0.2 A)$

 $R_{DS(on)3}$ = 2.98 Ω MAX. (VGS = -2.5 V, ID = -0.15 A)

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ648	SC-75 (USM)

Marking: H1

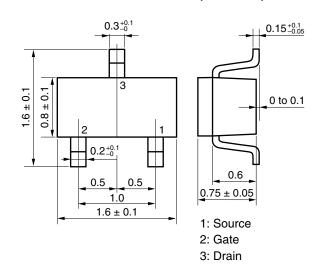
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Drain to Source Voltage (VGS = 0 V)	VDSS	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	∓12	V
Drain Current (DC)	ID(DC)	∓0.4	Α
Drain Current (pulse) Note1	ID(pulse)	∓1.6	Α
Total Power Dissipation Note2	PT	200	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

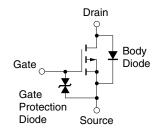
Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Mounted on ceramic substrate of 300 mm² x 0.64 mm.

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

V_{ESD} = ± 100 V TYP. (C = 200 pF, R = 0 Ω , Single pulse)

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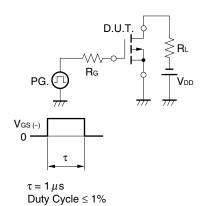


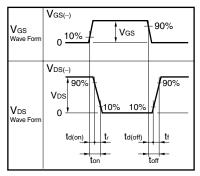
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -20 V, V _{GS} = 0 V			-1.0	μΑ
Gate Leakage Current	Igss	V _{GS} = ∓12 V, V _{DS} = 0 V			∓10	μА
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	-0.8	-1.3	-1.8	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = -10 V, I _D = -0.2 A	0.2	0.6		S
Drain to Source On-state Resistance Note	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -0.2 A		1.17	1.45	Ω
	RDS(on)2	V _{GS} = -4.0 V, I _D = -0.2 A		1.25	1.55	Ω
	RDS(on)3	V _{GS} = -2.5 V, I _D = -0.15 A		2.25	2.98	Ω
Input Capacitance	Ciss	V _{DS} = -10 V		29		pF
Output Capacitance	Coss	V _{GS} = 0 V		15		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		3.0		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -0.2 A		23		ns
Rise Time	tr	V _{GS} = -4.0 V		39		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		50		ns
Fall Time	t f			33		ns
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 0.4 A, V _{GS} = 0 V		0.93		V

Note Pulsed PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT SWITCHING TIME







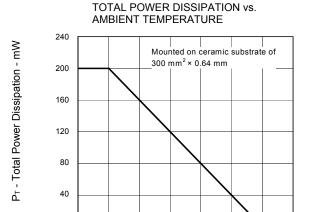
0

0

25

50

TYPICAL CHARACTERISTICS (TA = 25°C)



75 TA - Ambient Temperature - °C

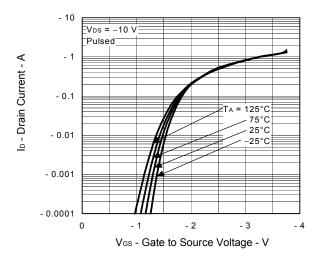
FORWARD TRANSFER CHARACTERISTICS

100

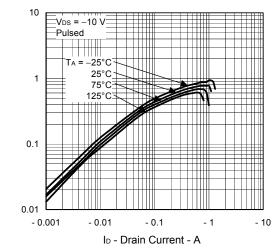
125

150

175

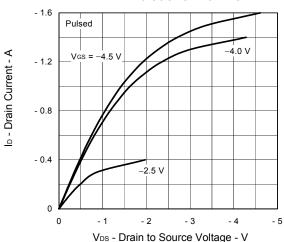


FORWARD TRANSFER ADMITTANCE vs. **DRAIN CURRENT**

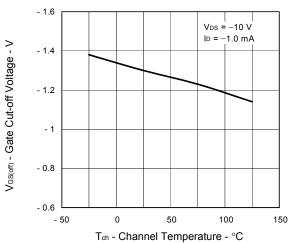


ys | - Forward Transfer Admittance - S

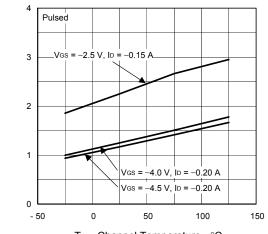
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



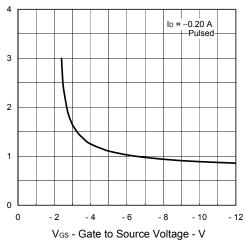
Tch - Channel Temperature - °C

 $\mathsf{R}_{\mathsf{DS}(m)}$ - Drain to Source On-state Resistance - Ω

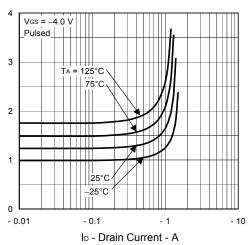
 $\mathsf{R}_{\mathsf{DS}(\varpi)}$ - Drain to Source On-state Resistance - Ω

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

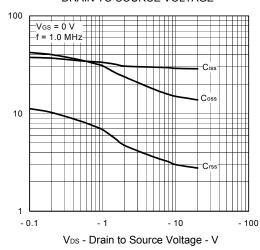
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



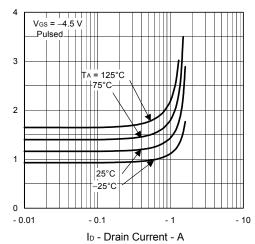
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



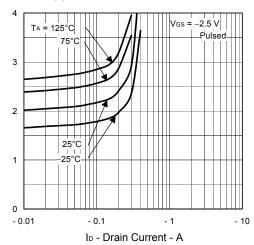
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



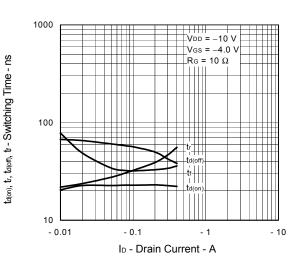
 $\mathsf{R}_{\mathsf{DS}(\varpi)}$ - Drain to Source On-state Resistance - Ω

 $\mathsf{Res}_{\text{(on)}}$ - Drain to Source On-state Resistance - Ω

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

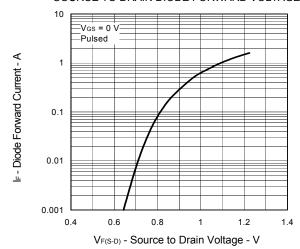


SWITCHING CHARACTERISTICS



Ciss, Coss, Crss - Capacitance - pF

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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